

Description

These N-channel enhancement mode power field effect transistors are using **shielded gate trench DMOS** technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- 110V, 300A, $R_{DS(on).max}=1.95m\Omega@V_{GS} = 10V$
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green device available

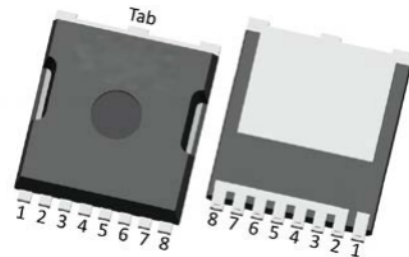
Applications

- Motor Drives
- UPS
- DC-DC Converter
- SR
- BMS

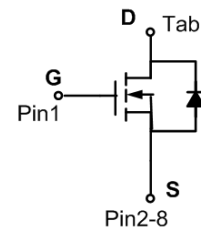
Product Summary

V_{DSS}	110V
$R_{DS(on).typ}@V_{GS}=10V$	1.62mΩ
I_D	300A

Pin Configuration



TOLL



N-channel MOSFET



Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	110	V
Continuous drain current ¹⁾ ($T_C = 25^\circ C$, Silicon limit)	I_D	324	A
($T_C = 25^\circ C$, Package limit)		300	A
($T_C = 100^\circ C$, Silicon limit)		229	A
Pulsed drain current ²⁾	I_{DM}	1200	A
Gate-Source voltage	V_{GS}	± 20	V
Avalanche energy ³⁾	E_{AS}	1024	mJ
Power Dissipation	P_D	429	W
Storage Temperature Range	T_{STG}	-55 to +175	$^\circ C$
Operating Junction Temperature Range	T_J	-55 to +175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.35	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient, minimal footprint ⁴⁾	$R_{\theta JA}$	62	$^\circ C/W$
Soldering temperature, wave soldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^\circ C$

Device	Device Package	Marking	Units/Reel
RSTG11R019	TOLL	RSTG11R019	2000

Electrical Characteristics

 $T_J = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	110	---	---	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3.25	4	V
Drain-source leakage current	I_{DSS}	$V_{DS}=110V, V_{GS}=0V, T_J = 25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=110V, V_{GS}=0V, T_J = 175^{\circ}\text{C}$	---	---	300	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=20V, V_{DS}=0V$	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-20V, V_{DS}=0V$	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=50A, T_J = 25^{\circ}\text{C}$	---	1.62	1.95	mΩ
		$T_J = 175^{\circ}\text{C}$	---	3.4	---	
Forward transconductance	g_{fs}	$V_{DS}=20V, I_D=50A$	---	98	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS}=55V, V_{GS}=0V,$ $f=100kHz$	---	8860	---	pF
Output capacitance	C_{oss}		---	2165	---	
Reverse transfer capacitance	C_{rss}		---	77.3	---	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=55V, V_{GS}=10V,$ $I_D=50A, R_g=10\Omega$	---	114	---	ns
Rise time	t_r		---	182.8	---	
Turn-off delay time	$t_{d(off)}$		---	172	---	
Fall time	t_f		---	85	---	
Gate resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	---	2.1	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DS}=55V, I_D=50A,$ $V_{GS}=10V$	---	42.6	---	nC
Gate to drain charge	Q_{gd}		---	41.9	---	
Gate charge total	Q_g		---	147.1	---	
Gate plateau voltage	$V_{plateau}$		---	5	---	V
Output Charge	Q_{oss}	$V_{DS}=55V, V_{GS}=0V$	---	210	---	nC
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	300	A
Pulsed Source Current	I_{SM}		---	---	1200	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=50A, T_J=25^{\circ}\text{C}$	---	---	1.1	V
Peak reverse recovery current	I_{rrm}	$I_S=50A, di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	3.71	---	A
Reverse Recovery Time	t_{rr}		---	77.9	---	ns
Reverse Recovery Charge	Q_{rr}		---	177.1	---	nC

Notes:

- Limited by maximum junction temperature and duty cycle.
- Repetitive Rating: Pulse width limited by maximum junction temperature.
- $V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=64A$, Starting $T_J=25^{\circ}\text{C}$.
- The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

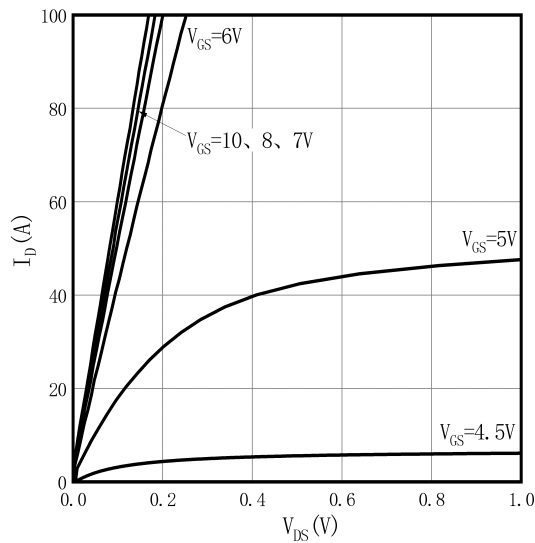


Figure 2. Transfer Characteristics

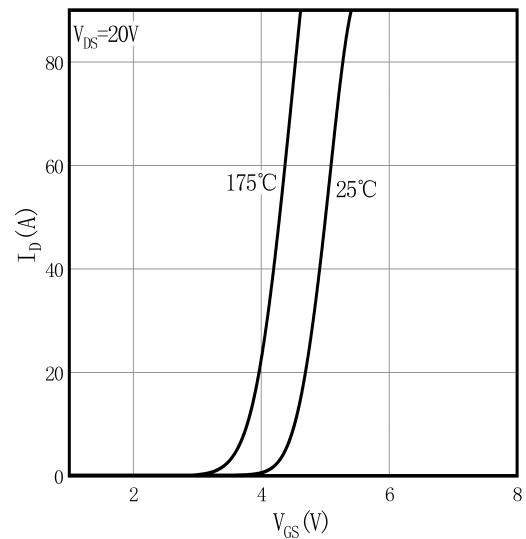


Figure 3. On-Resistance vs. Drain Current

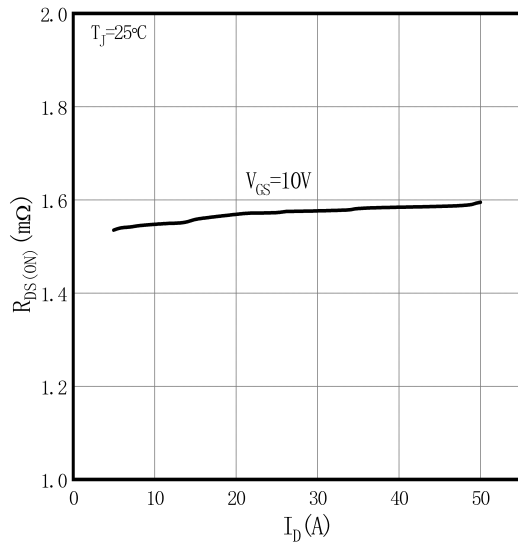


Figure 4. On-Resistance vs. Temperature

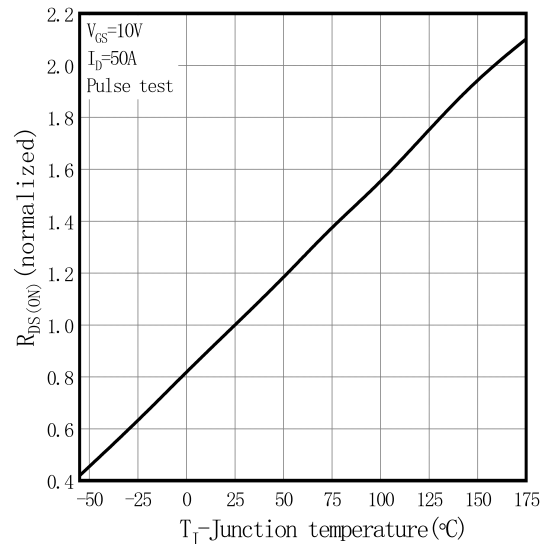


Figure 5. Breakdown Voltage vs. Temperature

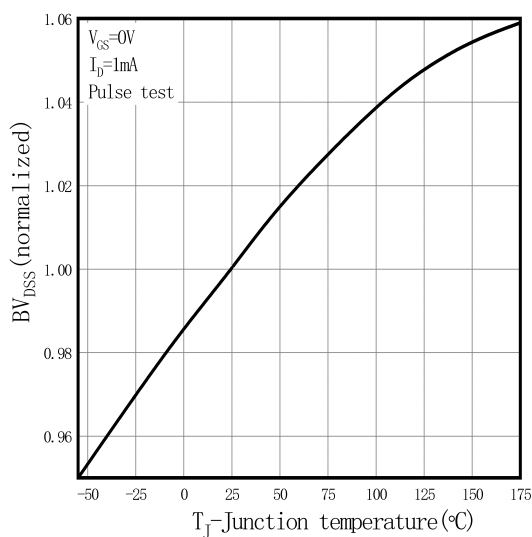


Figure 6. Threshold Voltage vs. Temperature

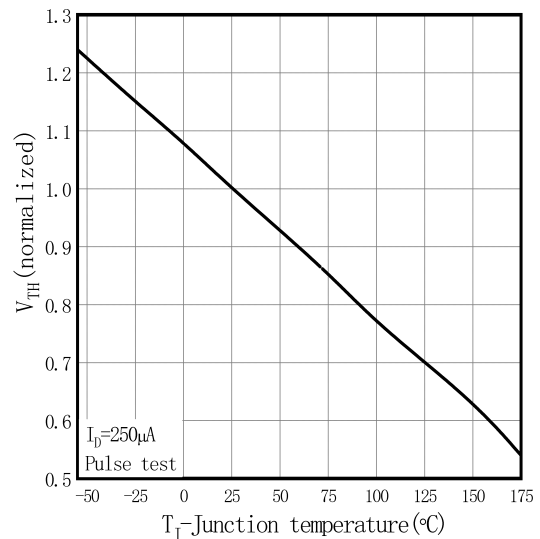


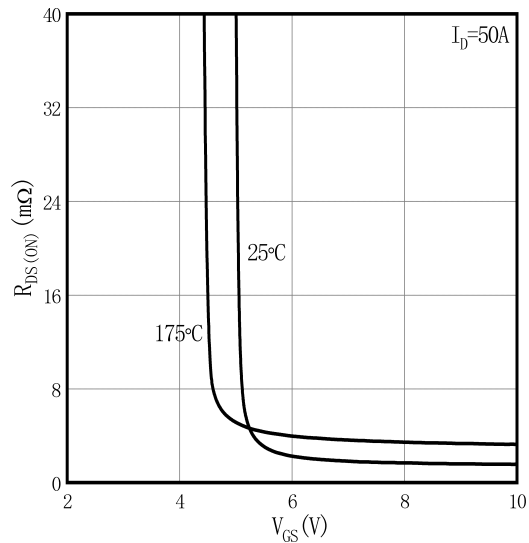
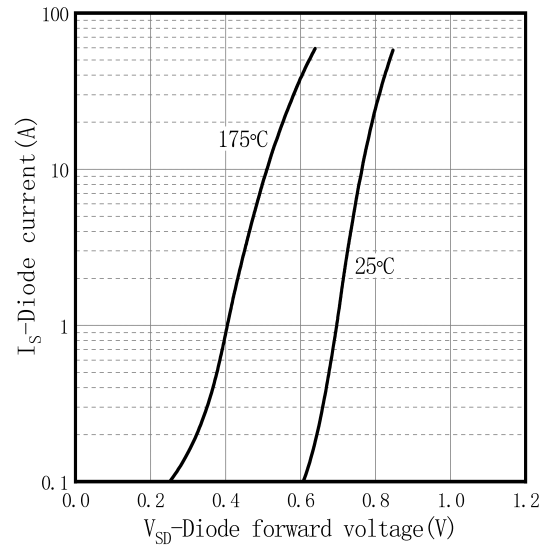
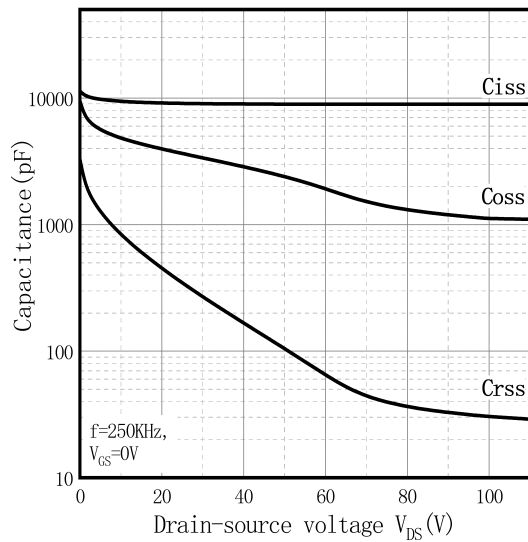
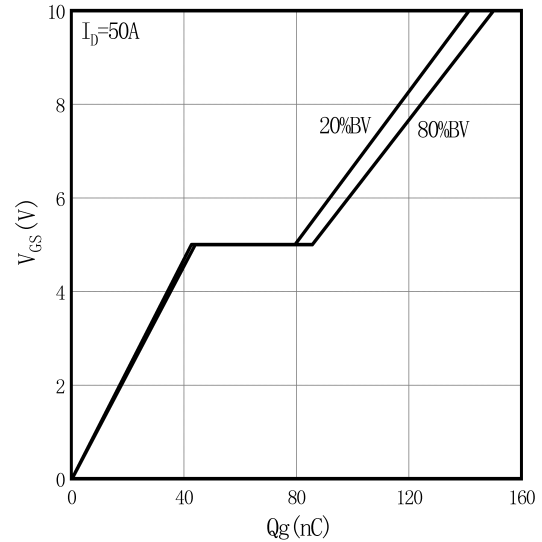
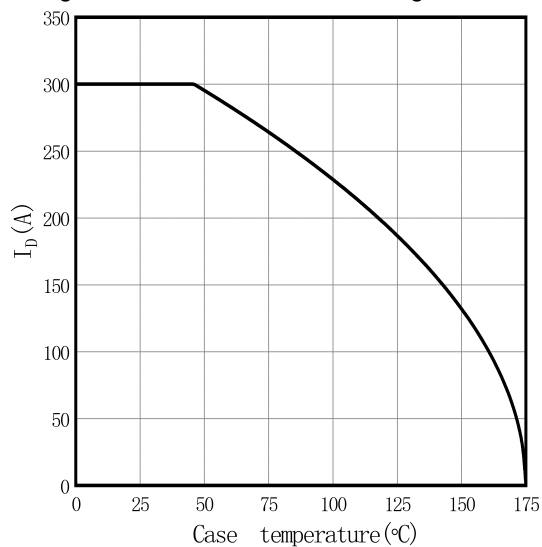
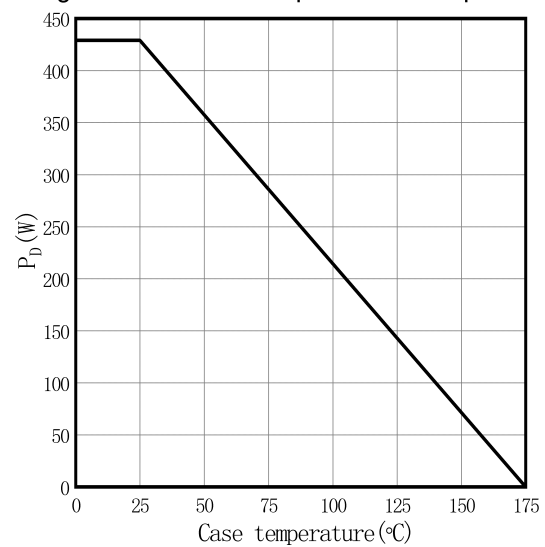
Figure 7. R_{ds(on)} vs. Gate Voltage

Figure 8. Body-Diode Characteristics

Figure 9. Capacitance Characteristics

Figure 10. Gate Charge Characteristics

Figure 11. Drain Current Derating

Figure 12. Power Dissipation vs. Temperature


Figure 13. Safe Operating Area

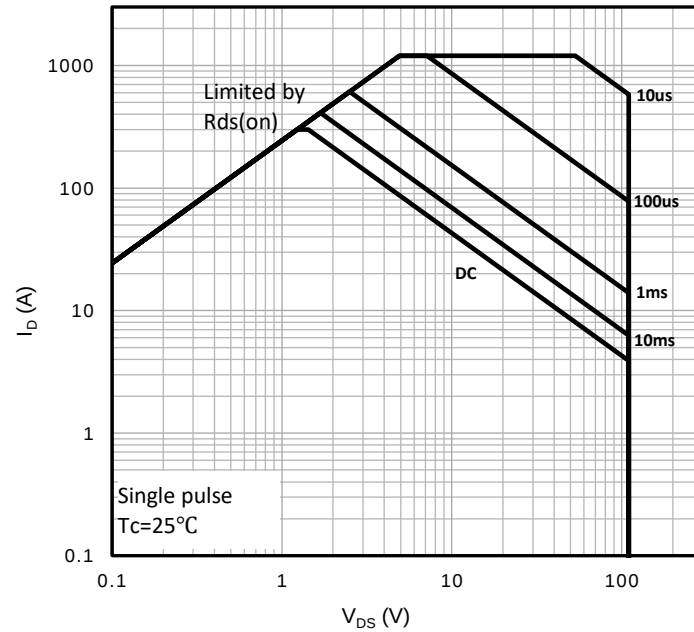
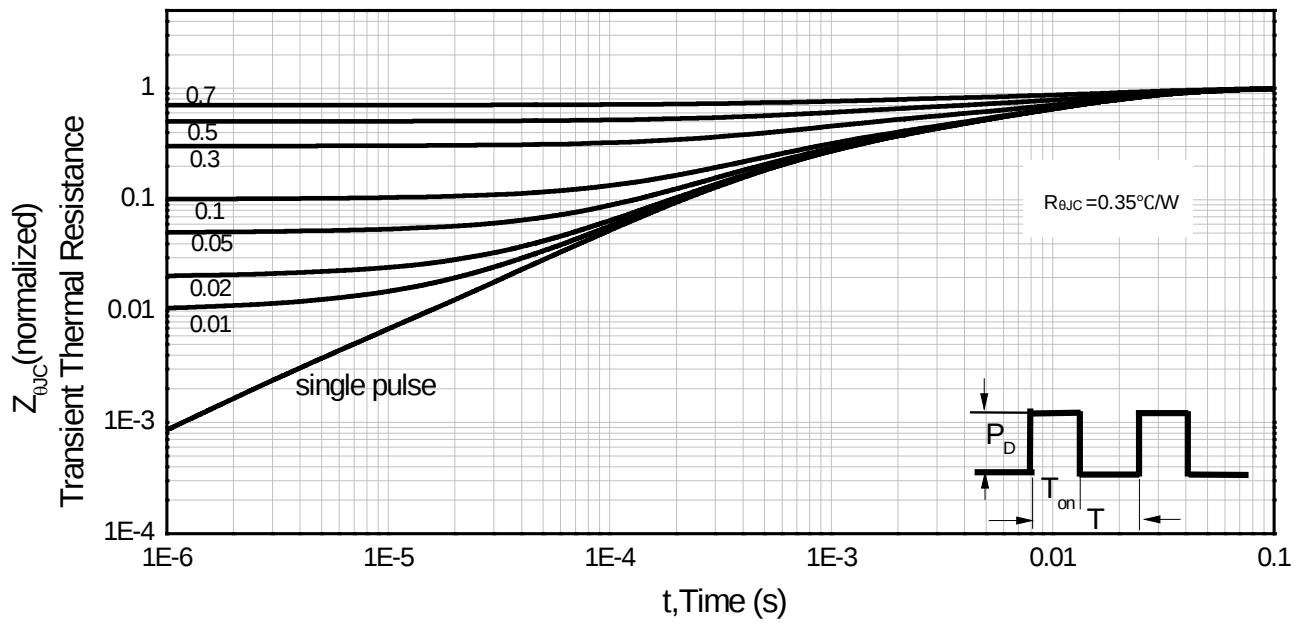
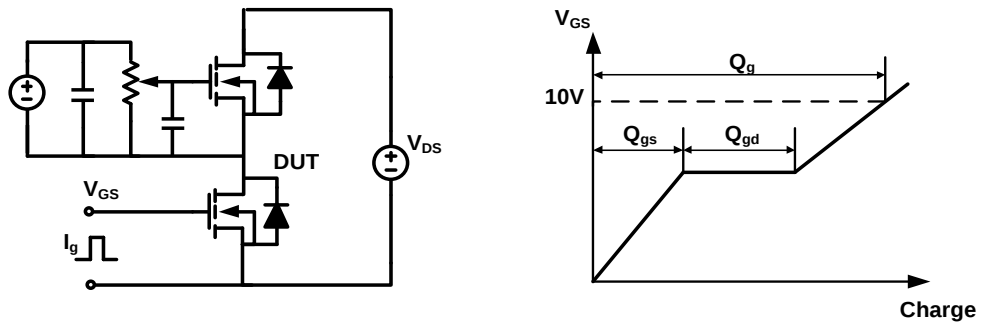


Figure 14. Normalized Maximum Transient Thermal Impedance (R_{thJC})

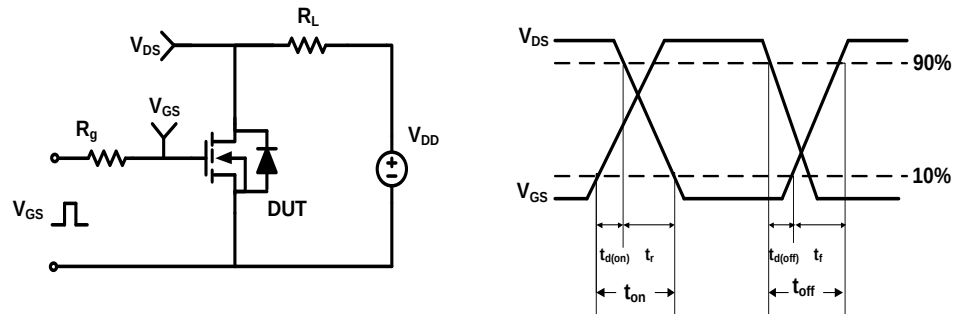


Waveforms

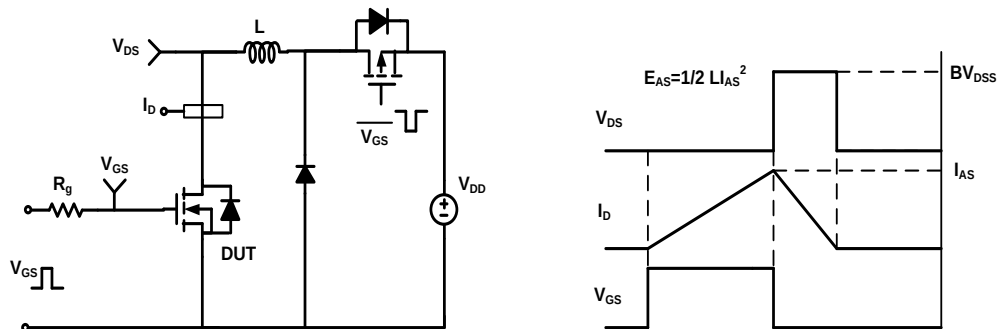
Gate Charge Test Circuit & Waveform



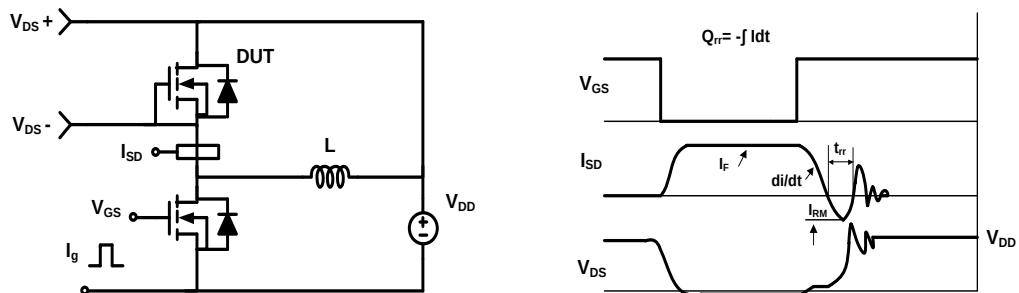
Resistive Switching Test Circuit & Waveform



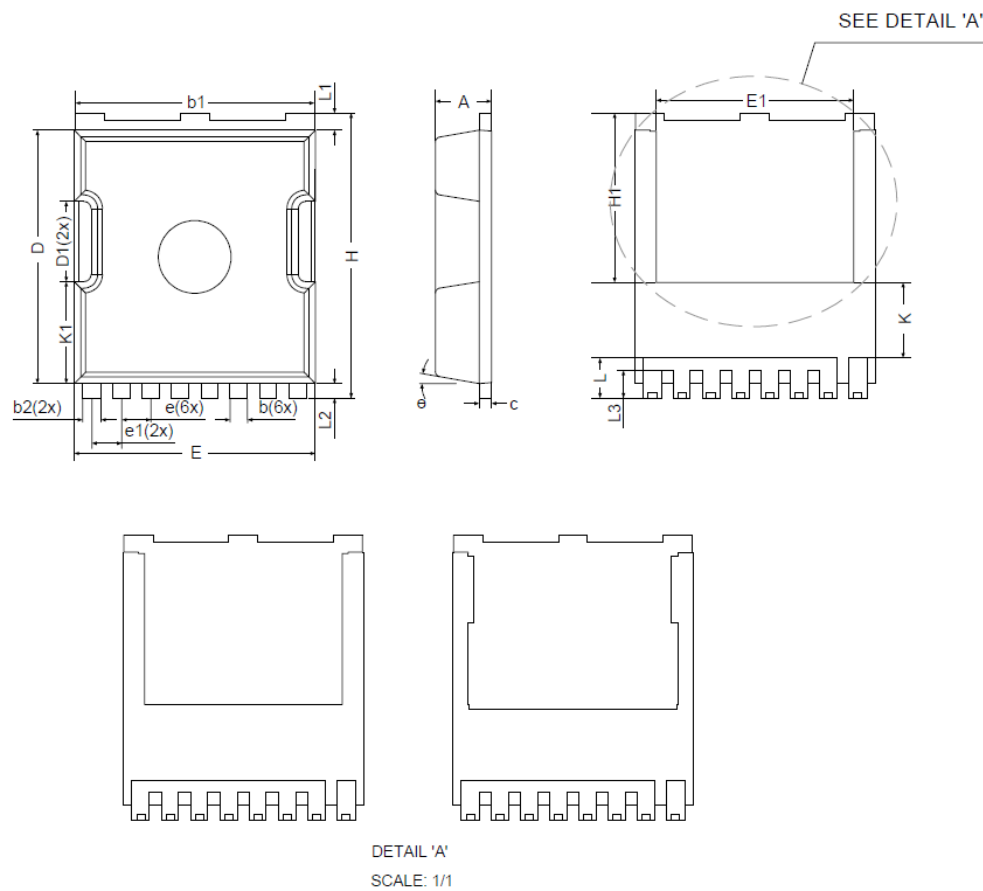
Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Diode Recovery Test Circuit & Waveform



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SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.15	2.45	0.085	0.096
b	0.60	0.90	0.024	0.035
b1	9.65	9.95	0.380	0.392
b2	0.65	0.90	0.026	0.035
c	0.40	0.60	0.016	0.024
D	10.18	10.58	0.401	0.417
D1	3.15	3.45	0.124	0.136
E	9.70	10.10	0.382	0.398
E1	7.90	8.40	0.311	0.331
e	1.10	1.30	0.043	0.051
e1	1.10	1.30	0.043	0.051
H	11.48	11.88	0.452	0.468
H1	6.75	7.30	0.266	0.287
K	2.45	3.33	0.096	0.131
K1	4.03	4.33	0.159	0.170
L	1.50	2.10	0.059	0.083
L1	0.50	0.90	0.020	0.035
L2	0.45	0.75	0.018	0.030
L3	1.00	1.30	0.039	0.051
θ	10° REF		10° REF	